

GSM3611P

30V P-Channel MOSFETs

Product Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

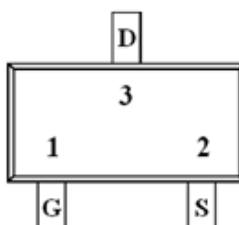
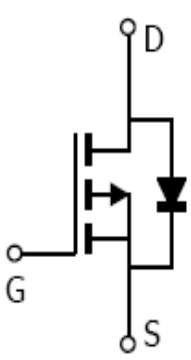
Features

- -30V, -4.1A, $R_{DS(ON)}=65m\Omega@V_{GS}=-10V$
- Fast switching
- Suit for -2.5V Gate Drive Applications
- Green Device Available
- SOT-23 package design

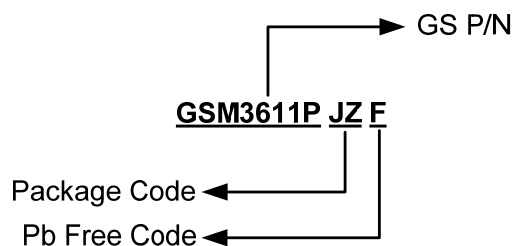
Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

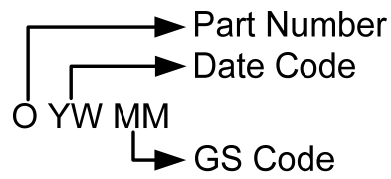
Packages & Pin Assignments

GSM3611PJZF (SOT-23)	
 <p>Top Views</p>	
	
Pin	Description
1	Gate
2	Source
3	Drain

Ordering Information



Marking Information



Part Number	Package	Part Marking	Quantity
GSM3611PJZF	SOT-23	OYWMM	3000pcs

Absolute Maximum Ratings

$T_A=25^\circ\text{C}$ Unless otherwise noted

Symbol	Parameter	Typical	Unit
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_A=25^\circ\text{C}$	-4.1
		$T_A=100^\circ\text{C}$	-2.6
I_{DM}	Pulsed Drain Current	-16.4	A
P_D	Power Dissipation ($T_A=25^\circ\text{C}$)	1.56	W
	Power Dissipation (Derate above 25°C)	0.012	W/ $^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	80	$^\circ\text{C}/\text{W}$

Electrical Characteristics

T_A=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30			V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA		-0.03		V/°C
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-0.4	-0.7	-0.9	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient			3		mV/°C
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±12V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V			-1	uA
		V _{DS} =-24V, V _{GS} =0V, T _J =125°C			-10	
I _S	Continuous Source Current	V _G =V _D =0V, Force Current			-4.1	A
I _{SM}	Pulsed Source Current				-16.4	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =-10V, I _D =-4A		55	65	mΩ
		V _{GS} =-4.5V, I _D =-3A		65	75	
		V _{GS} =-2.5V, I _D =-2A		85	100	
g _{FS}	Forward Transconductance	V _{DS} =-10V, I _D =-3A		5.4		S
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A			-1	V
Dynamic						
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-4A		8	11	nC
Q _{gs}	Gate-Source Charge			1.9	3	
Q _{gd}	Gate-Drain Charge			1.4	3	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz		810	1175	pF
C _{oss}	Output Capacitance			85	125	
C _{rss}	Reverse Transfer Capacitance			50	75	
t _{d(on)}	Turn-On Time	V _{DD} =-15V, I _D =-1A, V _{GS} =-10V, R _G =6Ω		5.4	10	ns
t _r				19.4	37	
t _{d(off)}	Turn-Off Time			45.9	87	
t _f				12.4	24	

Typical Performance Characteristics

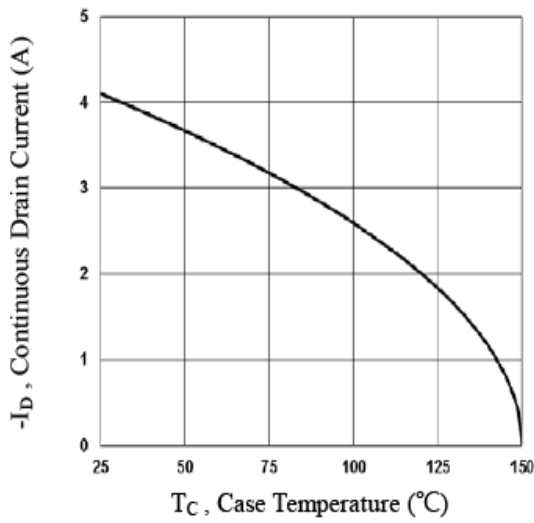


Fig.1 Continuous Drain Current vs. T_C

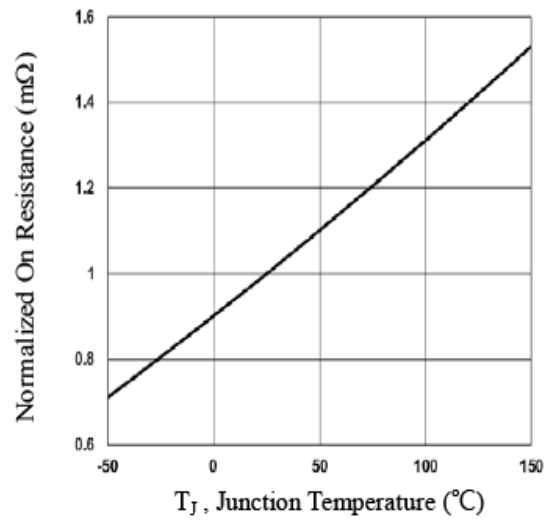


Fig.2 Normalized R_{DS(on)} vs. T_J

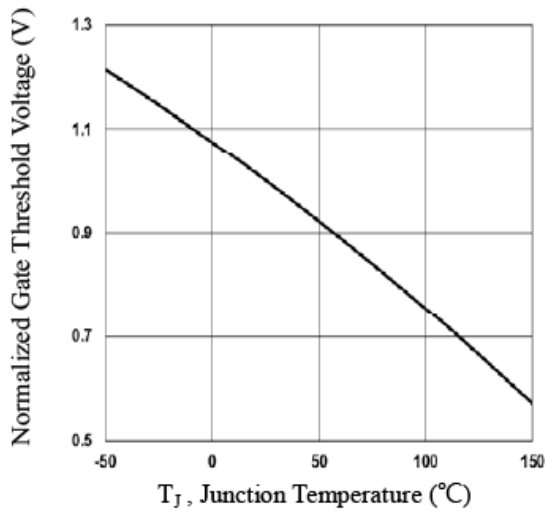


Fig.3 Normalized V_{th} vs. T_J

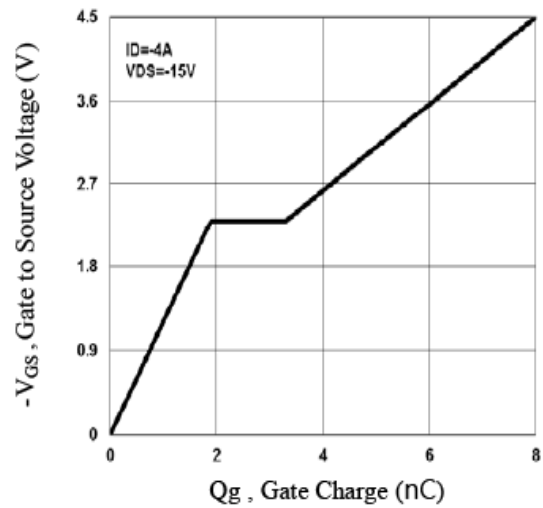


Fig.4 Gate Charge Waveform

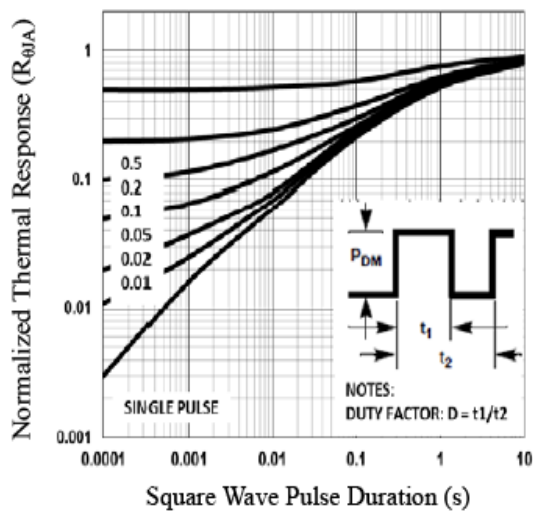


Fig.5 Normalized Transient Impedance

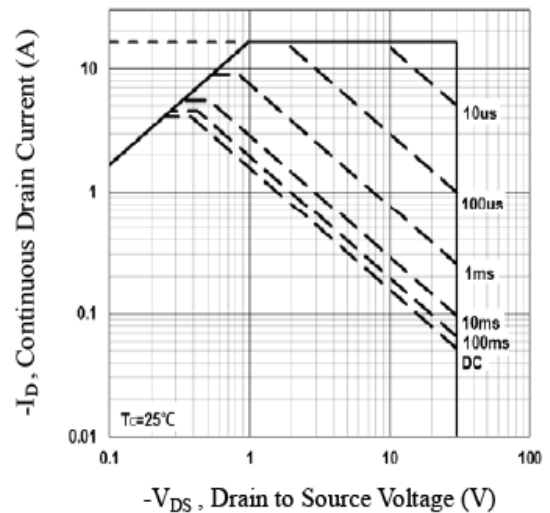
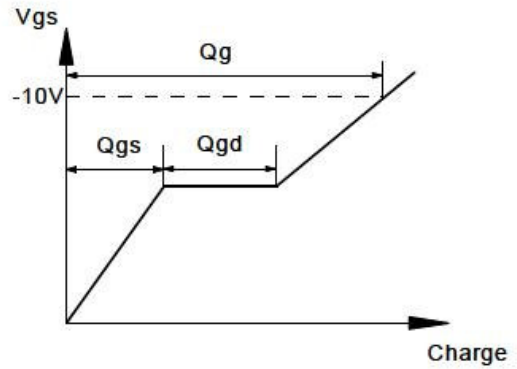
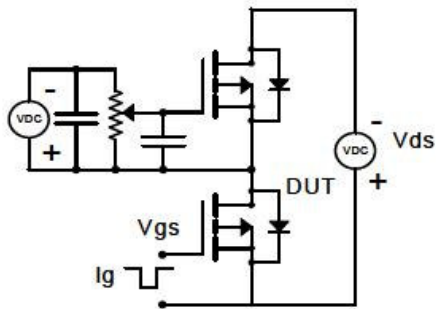


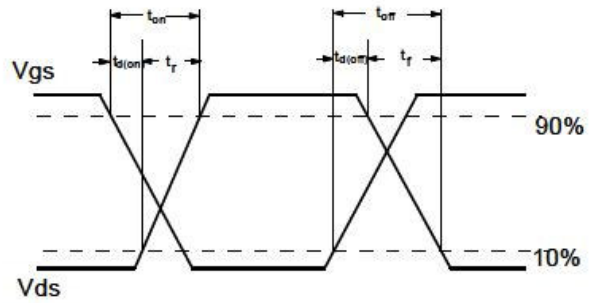
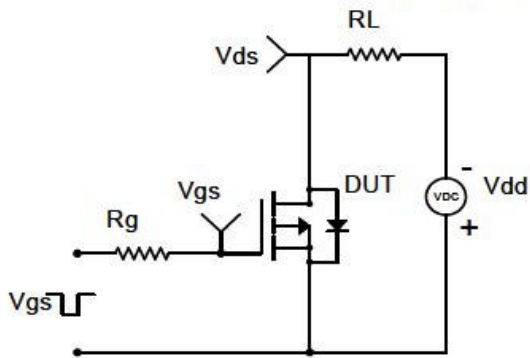
Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (Continue)

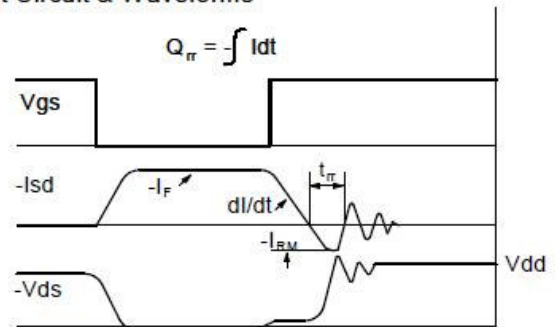
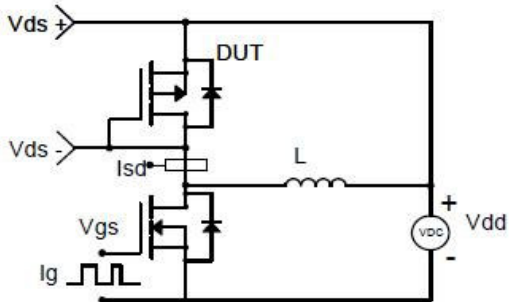
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

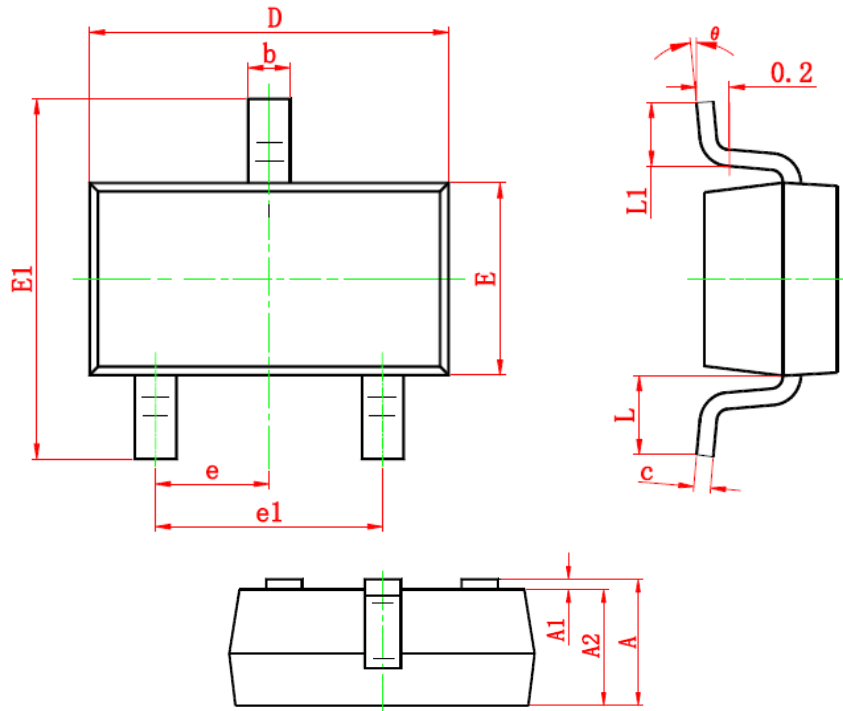


Diode Recovery Test Circuit & Waveforms



Package Dimension

SOT-23










Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°



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